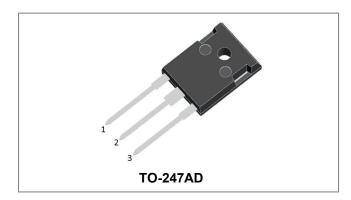






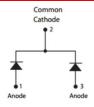
MBR80100WT SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	$V_{RRM} \ V_{RWM}$	-	100	V
DC Blocking Voltage	V_R			
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=105°C, rectangular wave form	40(Per Leg) 80(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	492	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 40A, Pulse, T _J = 25℃	0.85	0.87	V
(Per Leg)*	V _{F2}	@ 40A, Pulse, T _J = 125℃	0.78	0.80	V
Reverse Current	I _{R1}	@V _R = rated V _R ,T _J = 25℃	0.01	0.3	mA
(Per Leg)*	I _{R2}	@V _R = rated V _R ,T _J = 125℃	0.05	25.0	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25°C, f _{SIG} = 1MHz	500	1300	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*\,}$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

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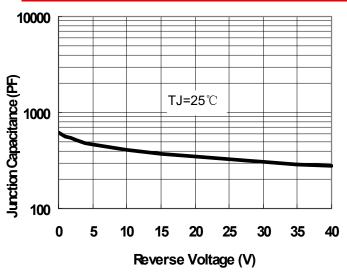


Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to	R ₀ JC	DC operation	0.8(Per Leg)	°C/W
Case			0.4(Per Device)	C/VV
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

10

Ratings and Characteristics Curves



Instantaneous Reverse Current-IR(MA) 1 TJ=125℃ 0.1 0.01 0.001 TJ=25℃ 0.0001 10 20 30 40 50 80 90 100 60 Percent of Rated Peak Reverse Voltage (%)

Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

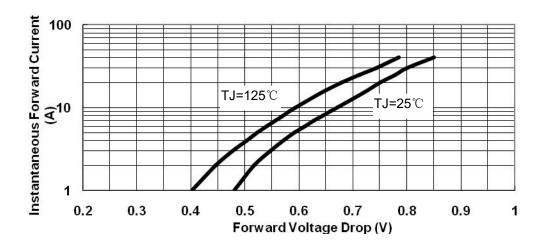


Fig.3-Typical Instantaneous Forward Voltage Characteristics

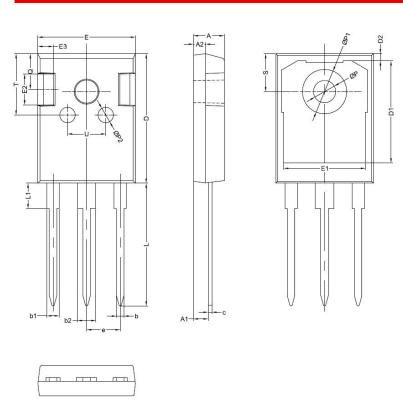
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Mechanical Dimensions TO-247AD



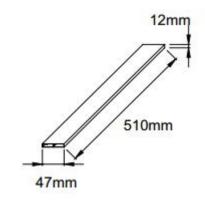
OVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.40	
b1	1.80	2.00	2.20	
b2	2.80	3.00	3.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.55		
D2		1.20		
Е	15.45	15.80	16.00	
 E1		13.30		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.70	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1		7.40	
P2		2.50		
Q		5.80		
Q S T	6.05	6.15	6.25	
T		10.00		
U		6.20		

Ordering Information:

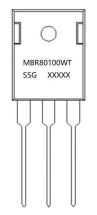
Device	Package	Shipping
MBR80100WT	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 80 = Forward Current (80A) 100 = Reverse Voltage (100V) WT = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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